

80V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	200A
V_{DSS}	80V
R_{DS(on)-typ}(@V_{GS}=10V)	<3.4mΩ(Typ:2.7 mΩ)

FEATURES

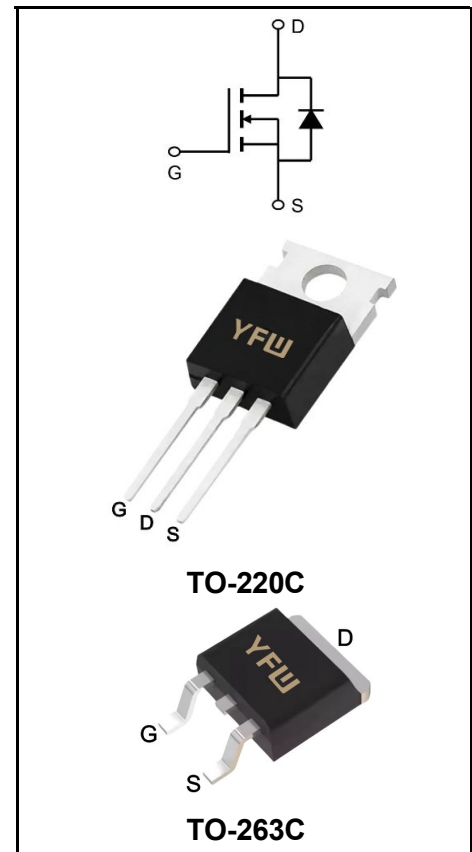
- ♦ Ultra-Low RDS(ON)
- ♦ Low Gate Charge
- ♦ High Current Capability

Application

- ♦ **YFW-SGT technology**
- ♦ Power Management in Telecom., Industrial Automa
- ♦ Motor Driving in Power Tool, E-vehicle, Robotics
- ♦ Current Switching in DC/DC&AC/DC(SR) Sub-sys

MECHANICAL DATA

- ♦ Case: TO-220C/AC, TO-263/ASC
- ♦ Mounting Position: Any
- ♦ Molded Plastic: UL Flammability Classification Rating 94V-0
- ♦ Lead free in compliance with EU RoHS 2011/65/EU directive
- ♦ Solder bath temperature 275°C maximum, 10s per JESD 22-B106



Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	80	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous drain current	I_D	200	A
Pulsed Drain Current (Note1)	I_{DM}	800	A
Power dissipation	P_D	268	W
Single Pulse Avalanche Energy(Note1)	E_{AS}	700	mJ
Operation and storage temperature	T_{STG}, T_J	-55 to +150	°C
Thermal Resistance, Junction-case	R_{θJC}	0.47	°C/W
Thermal Resistance, Junction to Ambient	R_{θJA}	34	°C/W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	80	-	-	V
Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V$	I_{DSS}	-	-	1	μA
Gate-Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I_{GSS}	-	-	± 100	nA
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10 V, I_D = 20 A$	$R_{DS(ON)}$	-	2.7	3.4	m Ω
Input Capacitance	$V_{GS}=0V$ $V_{DS}=40V$ $f=1MHz$	C_{iss}	-	7000	-	pF
Output Capacitance		C_{oss}	-	3500	-	
Reverse Transfer Capacitance		C_{rss}	-	250	-	
Turn-on delay time(Note2)	$V_{DS}=39V$ $V_{GS}=10V$ $R_G=6.2\Omega$ $I_D=20A$	$t_{d(on)}$	-	31	-	ns
Rise Time(Note2)		T_r	-	35	-	
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	61	-	
Fall Time(Note2)		t_f	-	31	-	
Total Gate Charge(Note2)	$I_D=20A$ $V_{DS}=40V$ $V_{GS}=10V$	Q_g	-	91	-	nC
Gate-Source Charge(Note2)		Q_{gs}	-	33	-	
Gate-Drain Charge(Note2)		Q_{gd}	-	18	-	
Diode forward current		I_S	-	-	200	A
Maximum Pulsed Body Diode Forward Current		I_{SM}			800	A
Diode Forward Voltage	$V_{GS}=0V, I_S=20A, T_J=25^\circ C$	V_{SD}	-	-	1.2	V
Reverse Recovery Time(Note2)	$I_F=20A, di/dt = 100 A/\mu s$	t_{rr}	-	75	-	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	155	-	nC

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

Ratings and Characteristic Curves

Figure 1: Power De-rating

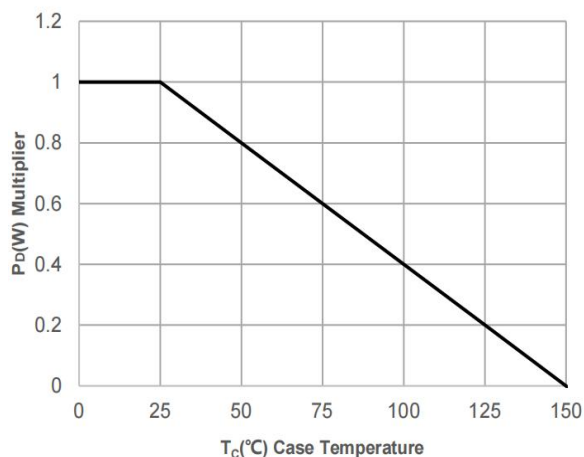


Figure 2: Current De-rating

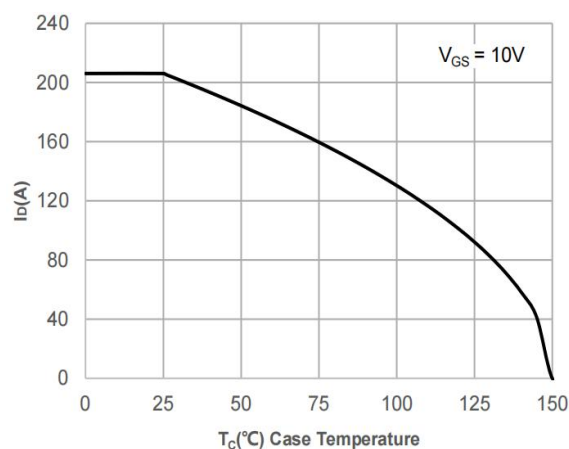


Figure 3: Normalized Maximum Transient Thermal Impedance

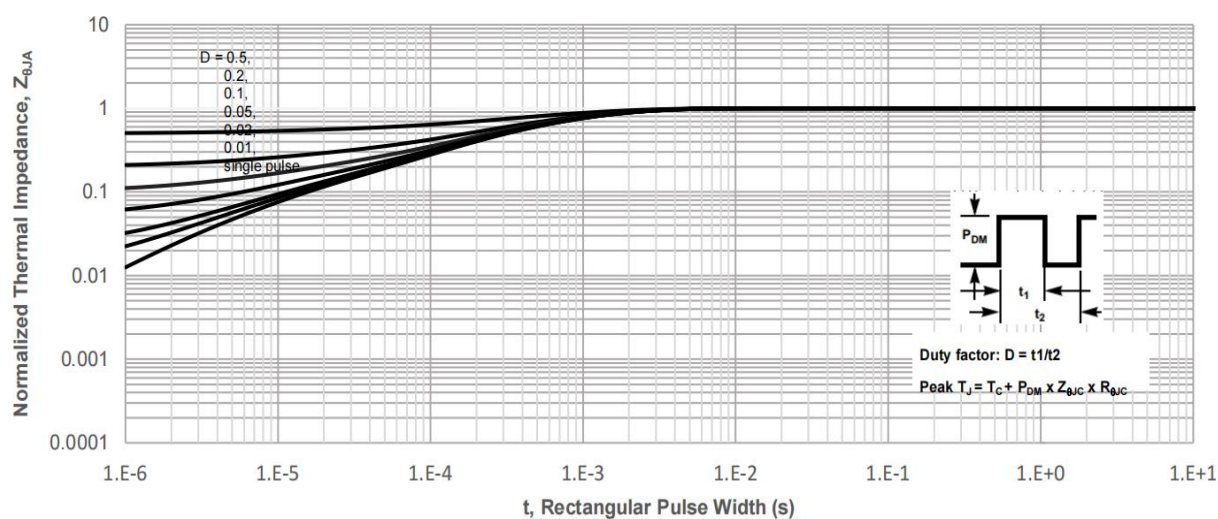
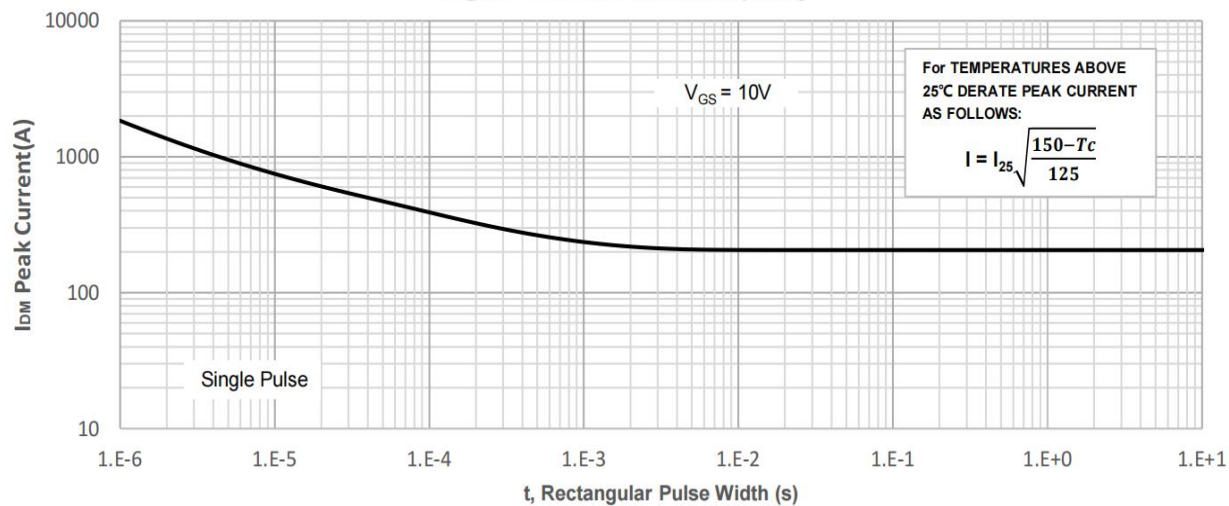


Figure 4: Peak Current Capacity



Ratings and Characteristic Curves

Figure 5: Output Characteristics

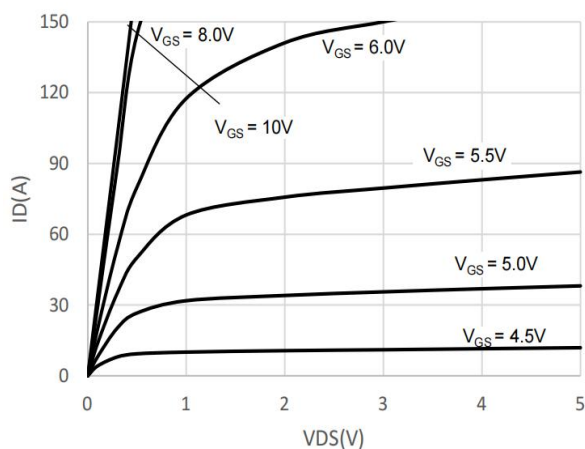


Figure 6: Typical Transfer Characteristics

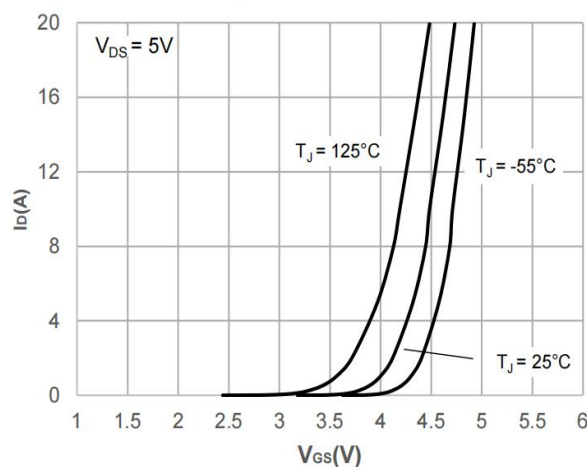


Figure 7: On-resistance vs. Drain Current

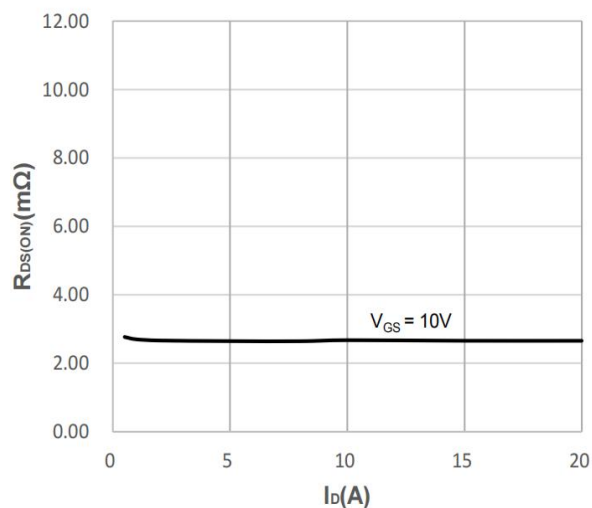


Figure 8: Body Diode Characteristics

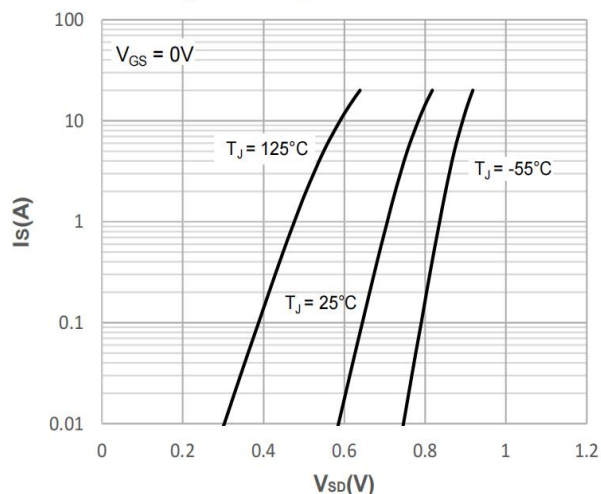


Figure 9: Gate Charge Characteristics

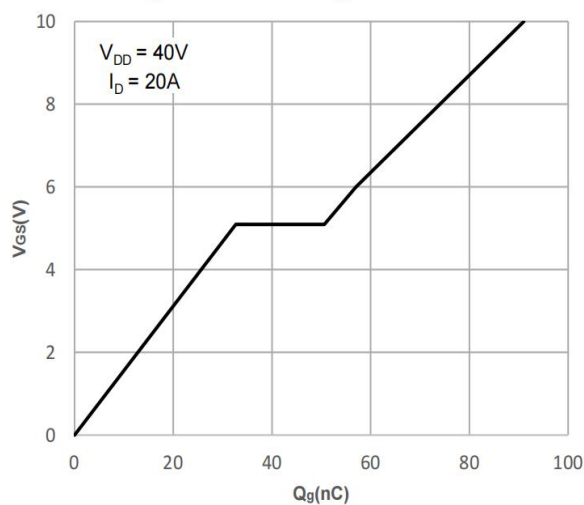
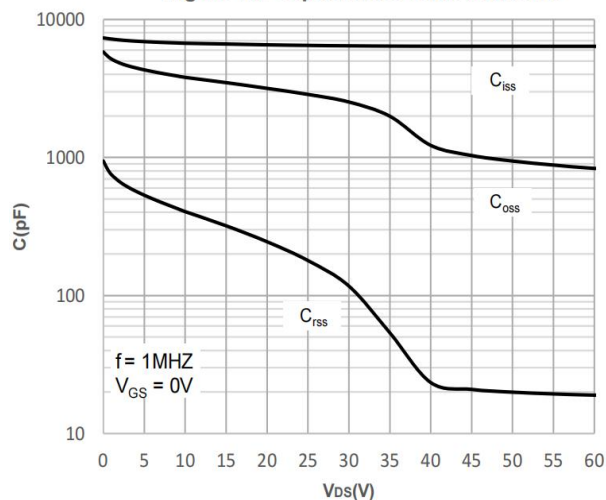


Figure 10: Capacitance Characteristics



RATINGS AND CHARACTERISTIC CURVES

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

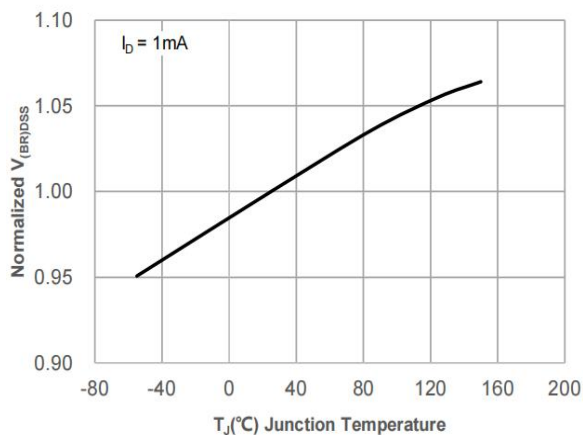


Figure 12: Normalized on Resistance vs. Junction Temperature

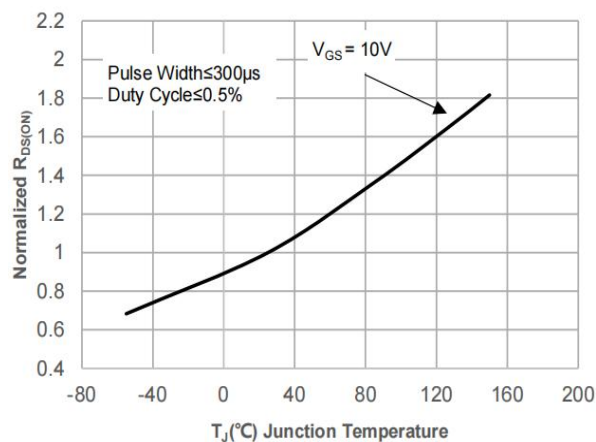


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

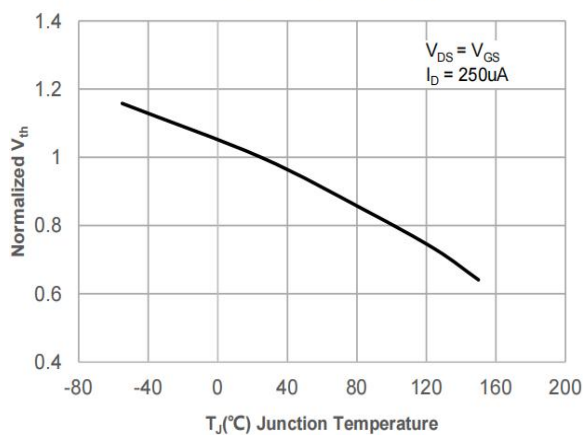


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

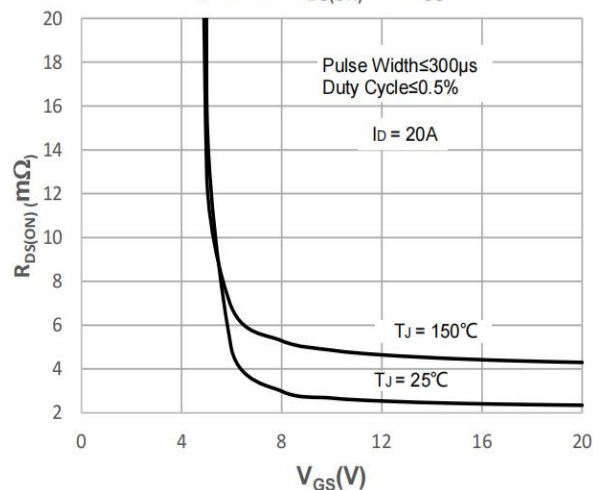
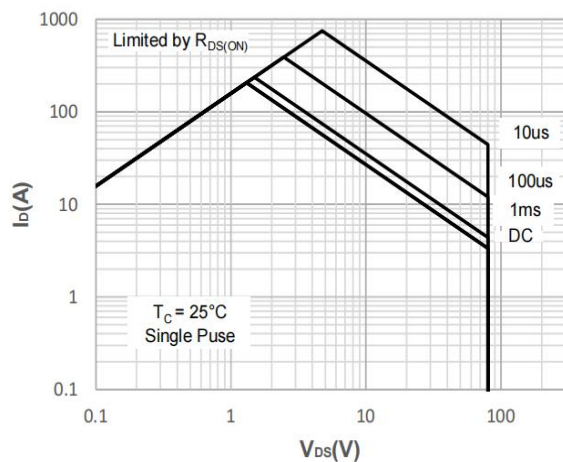
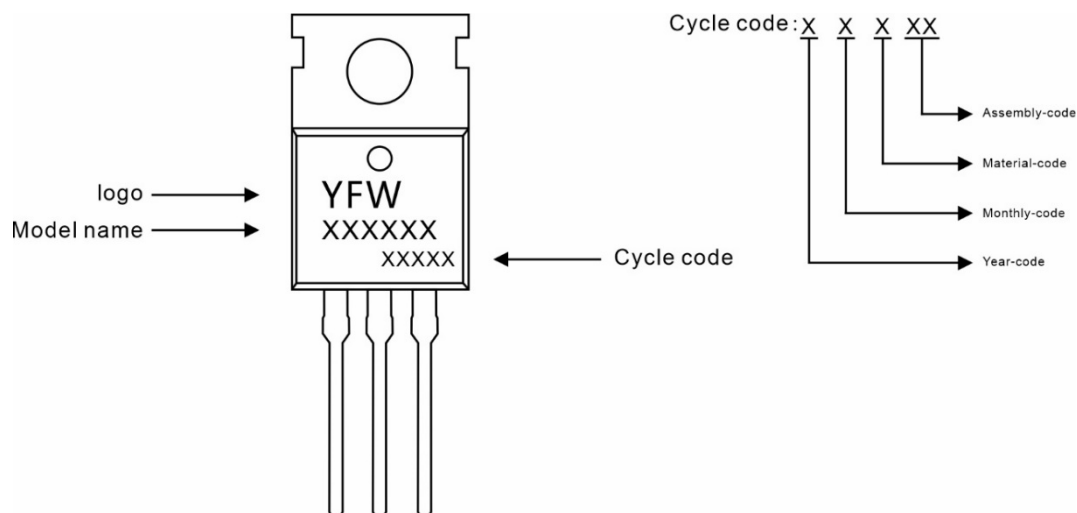


Figure 15: Maximum Safe Operating Area



Marking Diagram



Ordering information

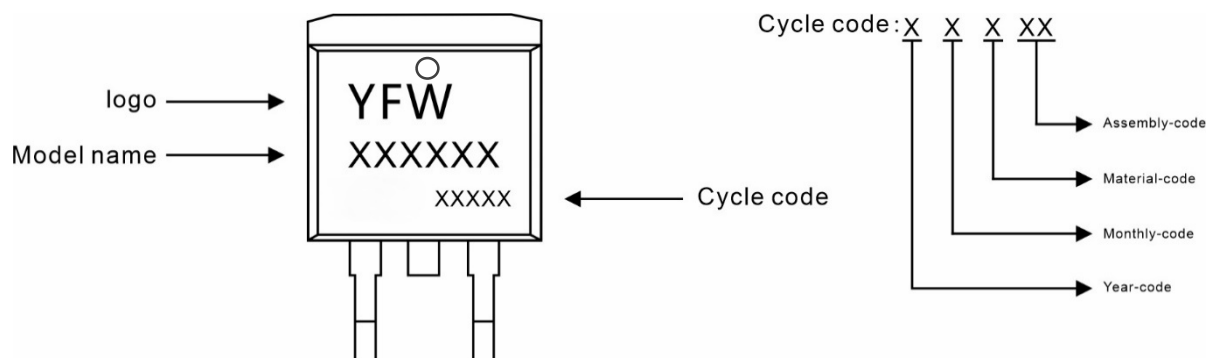
Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG200N08AC	TO-220C	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions

TO-220C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG200N08ASC	TO-263C	0.04oz(1.16g)	800pcs/reel	1600pcs/box 8000pcs/Carton

Package Dimensions

TO-263C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A1	0.00	0.15	0.000	0.006
A2	4.30	4.55	0.169	0.179
B	1.10	1.50	0.043	0.059
b	0.70	0.90	0.028	0.035
b1	1.20	1.50	0.047	0.059
c	0.30	0.60	0.012	0.024
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
L	15.00	15.30	0.591	0.602
L1	5.20	5.40	0.205	0.213
L2	2.40	2.60	0.094	0.102
L3	1.60	1.80	0.063	0.071

Disclaimer

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